## TOSHIBA

Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2949

#### Chopper Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance  $: R_{DS} (ON) = 0.4 \Omega (typ.)$
- High forward transfer admittance  $|Y_{fs}| = 8.0 \text{ S (typ.)}$
- Low leakage current  $: IDSS = 100 \ \mu A \ (max) \ (VDS = 400 \ V)$
- Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

#### Maximum Ratings (Ta = 25°C)

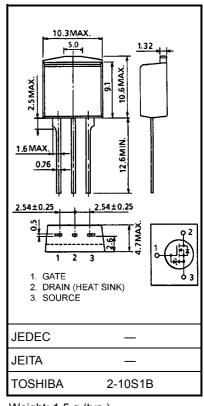
| Characteris                               | stics                  | Symbol           | Rating  | Unit |  |
|---|------------------------|------------------|---------|------|--|
| Drain-source voltage                      |                        | V <sub>DSS</sub> | 400     | V    |  |
| Drain-gate voltage (R                     | <sub>GS</sub> = 20 kΩ) | V <sub>DGR</sub> | 400     | V    |  |
| Gate-source voltage                       |                        | V <sub>GSS</sub> | ±30     | V    |  |
| Drain current                             | DC (Note 1)            | ۱ <sub>D</sub>   | 10      | А    |  |
|   | Pulse (Note 1)         | I <sub>DP</sub>  | 40      | А    |  |
| Drain power dissipation                   | n (Tc = 25°C)          | PD               | 80      | W    |  |
| Single pulse avalanche energy<br>(Note 2) |                        | E <sub>AS</sub>  | 360     | mJ   |  |
| Avalanche current                         |                        | I <sub>AR</sub>  | 10      | А    |  |
| Repetitive avalanche e                    | energy (Note 3)        | E <sub>AR</sub>  | 8       | mJ   |  |
| Channel temperature                       |                        | T <sub>ch</sub>  | 150     | °C   |  |
| Storage temperature ra                    | ange                   | T <sub>stg</sub> | -55~150 | °C   |  |

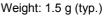
### **Thermal Characteristics**

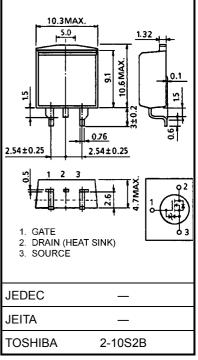
| Characteristics                        | Symbol                 | Max  | Unit   |
|--|------------------------|------|--------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 1.56 | °C / W |
| Thermal resistance, channel to ambient | R <sub>th (ch−a)</sub> | 83.3 | °C / W |

- Note 1: Please use devices on condition that the channel temperature is below 150°C.
- Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 5.85 mH,  $R_G$  = 25  $\Omega$ , I<sub>AR</sub> = 10 A
- Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.







Weight: 1.5 g (typ.)

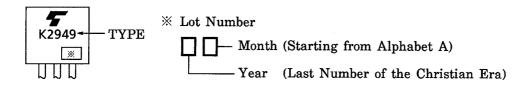
Electrical Characteristics (Ta = 25°C)

| Charac  | teristics       | Symbol               | Test Condition   | Min | Тур. | Max  | Unit |
|---|-----------------|----------------------|--|-----|------|------|------|
| Gate leakage cu                                 | rrent           | I <sub>GSS</sub>     | $V_{GS}$ = ±25 V, $V_{DS}$ = 0 V   | _   | —    | ±10  | μA   |
| Gate-source bre                                 | eakdown voltage | V (BR) GSS           | $I_{G} = \pm 10 \ \mu A, V_{DS} = 0 \ V$   | ±30 | _    | _    | V    |
| Drain cut-off cu                                | rrent           | I <sub>DSS</sub>     | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V   |     | —    | 100  | μA   |
| Drain-source br                                 | eakdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V  | 400 | _    |      | V    |
| Gate threshold v                                | voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 2.0 | _    | 4.0  | V    |
| Drain-source O                                  | N resistance    | R <sub>DS (ON)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.0 A   |     | 0.4  | 0.55 | Ω    |
| Forward transfer                                | admittance      | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.0 A   | 4.0 | 8.0  |      | S    |
| Input capacitance                               | e               | C <sub>iss</sub>     |  |     | 1340 |      |      |
| Reverse transfer capacitance                    |                 | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz   |     | 160  |      | pF   |
| Output capacitance                              |                 | C <sub>oss</sub>     |  |     | 490  |      |      |
| Switching time                                  | Rise time       | tr                   | $V_{GS} \stackrel{10 \text{ V}}{_{0 \text{ V}}} \prod_{\substack{O \text{ V} \\ O \text{ C} \\ \downarrow \\ $ | _   | 22   | -    |      |
|   | Turn-on time    | t <sub>on</sub>      |  | _   | 60   | -    | ns   |
|   | Fall time       | t <sub>f</sub>       |  | _   | 32   | -    | 115  |
|   | Turn-off time   | t <sub>off</sub>     | Duty $\leq 1\%$ , t <sub>w</sub> = 10 µs   | _   | 140  | _    |      |
| Total gate charge (gate-source plus gate-drain) |                 | Qg                   |  | _   | 34   | _    |      |
| Gate-source charge                              |                 | Q <sub>gs</sub>      | V <sub>DD</sub> ≈ 320 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A   |     | 18   | _    | nC   |
| Gate-drain ("miller") Charge                    |                 | Q <sub>gd</sub>      |  |     | 16   | —    |      |

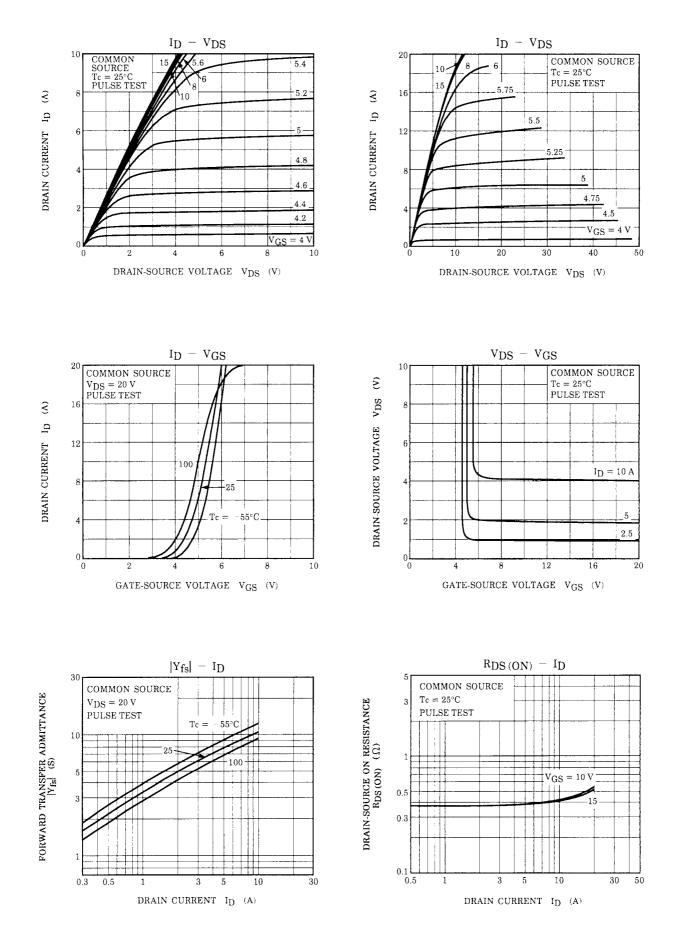
#### Source–Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                              | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|--|------------------|---|-----|------|------|------|
| Continuous drain reverse current<br>(Note 1) | I <sub>DR</sub>  | —   | _   | _    | 10   | А    |
| Pulse drain reverse current<br>(Note 1)      | I <sub>DRP</sub> | —   | _   | _    | 40   | А    |
| Forward voltage (diode)                      | V <sub>DSF</sub> | I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time                        | t <sub>rr</sub>  | I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V |     | 350  |      | ns   |
| Reverse recovery charge                      | Q <sub>rr</sub>  | dI <sub>DR</sub> / dt = 100 Å / µs            |     | 2.6  |      | μC   |

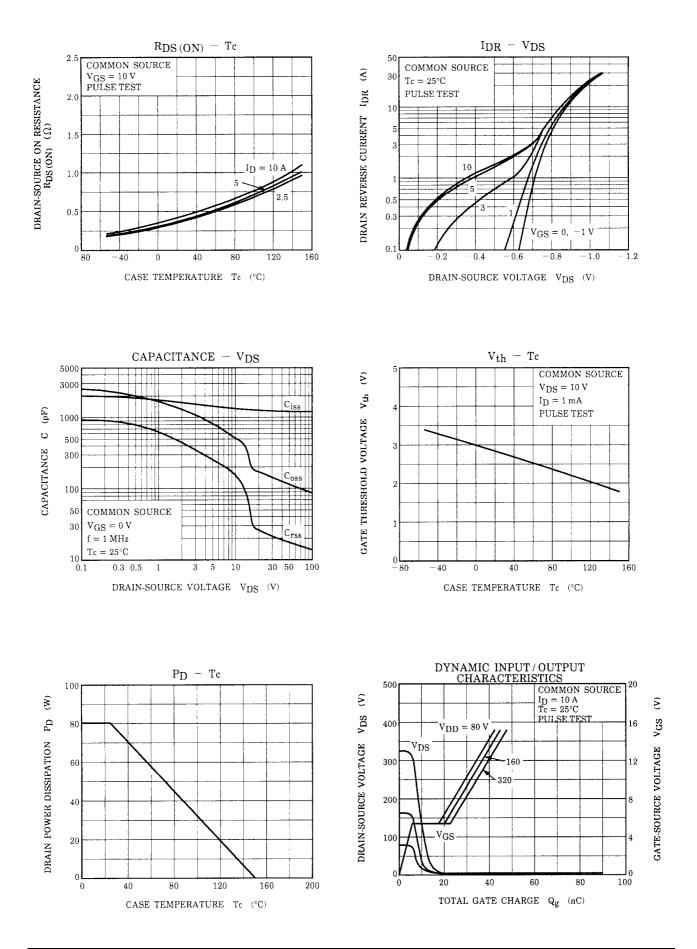
#### Marking

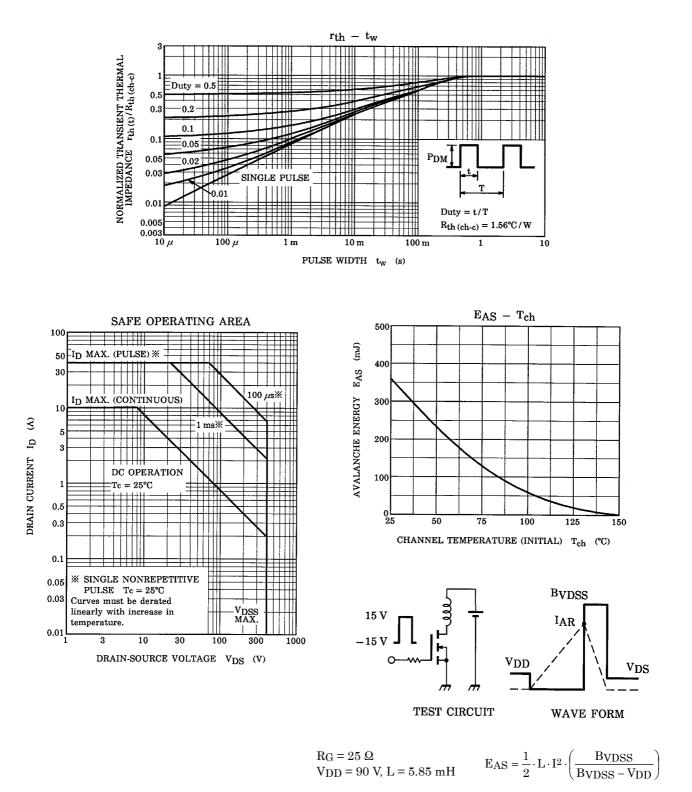


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